



## Features

- High Speed Switching with Low Capacitances
- High Blocking Voltage with Low  $R_{DS(on)}$
- Easy to parallel
- Simple to drive
- RoHS Compliant

## Benefits

- Increased Power Density
- Faster Operating Frequency
- Reduction of Heat Sink Requirements
- Higher Efficiency
- Reduced EMI

## Applications

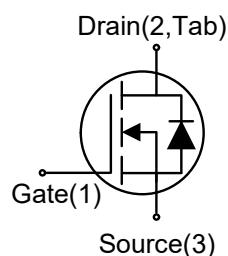
- Power Factor Correction Modules
- Switch Mode Power Supplies
- DC-AC Inverters
- High Voltage DC/DC Converters



Ordering Part Number	Package	Brand
SM360R65CT2TL	TO-220F	HXY MOSFET



TO-220F



## Maximum Ratings ( $T_c = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Value	Unit	Test Conditions
$V_{DS\text{max}}$	Drain - Source Voltage	650	V	$V_{GS} = 0 \text{ V}$ , $I_D = 100 \mu\text{A}$
$V_{GS\text{max}}$	Gate - Source Voltage (dynamic)	-5/+26	V	AC ( $f > 1 \text{ Hz}$ )
$V_{GS\text{op}}$	Gate - Source Voltage (static)	0/+18	V	Static
$I_D$	Continuous Drain Current	15	A	$T_c = 25^\circ\text{C}$
		12		$T_c = 100^\circ\text{C}$
$I_{DM}$	Pulsed Drain Current	39	A	Pulse width $t_p$ limited by $T_{j\text{max}}$
$P_D$	Power Dissipation	52	W	$T_c = 25^\circ\text{C}$
		25		$T_c = 100^\circ\text{C}$
$T_j$ , $T_{stg}$	Operating Junction and Storage Temperature	-55 to +175	°C	



**Electrical Characteristics** ( $T_c = 25^\circ\text{C}$  unless otherwise specified)

**Static Characteristics**

Symbol	Parameter	Test conditions	Value			Unit
			Min.	Typ.	Max.	
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$I_D=1\text{ mA}$ , $V_{GS}=0\text{V}$	650			V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS}=850\text{V}$ , $V_{GS}=0\text{V}$		1	15	$\mu\text{A}$
$I_{GSS}$	Gate-Source Leakage Current	$V_{DS}=0\text{V}$ , $V_{GS}=18\text{V}$			50	$\text{m}\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$ , $I_D=1\text{mA}$ $T_j=25^\circ\text{C}$ $T_j=175^\circ\text{C}$		3.5 2.8	4	V
$R_{DS(on)}$	Drain-Source On-State Resistance	$V_{GS}=18\text{V}$ , $I_D=4.5\text{A}$ $T_j=25^\circ\text{C}$ $T_j=175^\circ\text{C}$		180 205	220	$\text{m}\Omega$
	Drain-Source On-State Resistance	$V_{GS}=15\text{V}$ , $I_D=4.5\text{A}$ $T_j=25^\circ\text{C}$ $T_j=175^\circ\text{C}$		260 295	300	nA
$C_{iss}$	Input Capacitance	$V_{DS}=400\text{V}$ , $f=1\text{MHz}$ , $V_{GS}=0\text{V}$		180		$\text{pF}$
$C_{oss}$	Output Capacitance			20		$\text{pF}$
$C_{rss}$	Reverse Transfer Capacitance			0.9		$\text{pF}$
$Q_g$	Total Gate Charge	$V_{DS}=400\text{V}$ , $I_D=5\text{A}$ , $R_G = 10\ \Omega$ $V_{GS} = 0/15\text{V}$		11.2		nC
$Q_{gs}$	Gate to Source Charge			2.3		nC
$Q_{gd}$	Gate to Drain Charge			1.1		nC
$t_{d(on)}$	Turn-On Delay Time	$V_{DD}=400\text{V}$ , $I_D=5\text{A}$ , $V_{GS}=-5/18\text{V}$ , $R_G=10\Omega$ ,		5		ns
$t_r$	Rise Time			17		ns
$t_{d(off)}$	Turn-Off Delay Time			8		ns
$t_f$	Fall Time			10		ns
$E_{on}$	Turn-On Energy			25		$\mu\text{J}$
$E_{off}$	Turn-Off Energy			10		$\mu\text{J}$



### Reverse Diode Characteristics

Symbol	Parameter	Test conditions	Value			Unit
			Min.	Typ.	Max.	
$V_{SD}$	Diode Forward Voltage	$V_{GS}=-4V$ , $I_{SD}=2.5A$ $T_j=25^\circ C$ $T_j=175^\circ C$		4.0 3.6		V
$I_s$	Continuous Diode Forward Current	$T_c=25^\circ C$ $T_c=100^\circ C$		15 12		A
$t_{rr}$	Reverse Recovery Time	$I_{SD}=-5A$ $V_{GS}=-5V$ , $I_{SD}=4.5A$ ,		50		ns
$Q_{rr}$	Reverse Recovery Charge	$V_R=400V$ , $di/dt=1000A/\mu s$		38		nC
$I_{rrm}$	Peak Reverse Recovery Current			2.4		A

### Thermal Characteristics

Symbol	Parameter	Value			Unit
		Min.	Typ.	Max.	
$R_{th(j-c)}$	Thermal Resistance from Junction to Case		2.88		°C/W
$R_{th(j-a)}$	Thermal Resistance from Junction to Ambient		40		°C/W



## Typical Performance

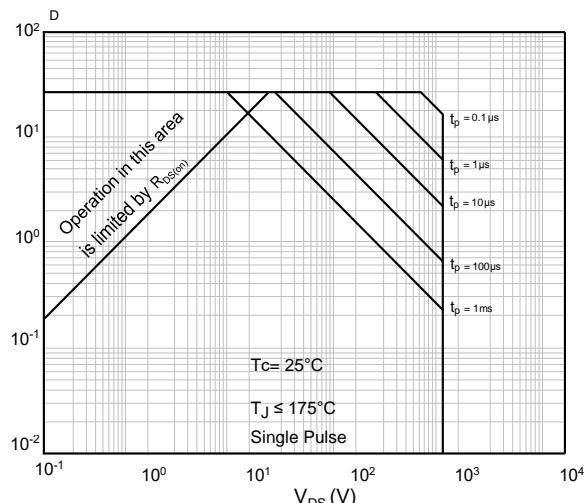


Figure 1. Safe Operating Area

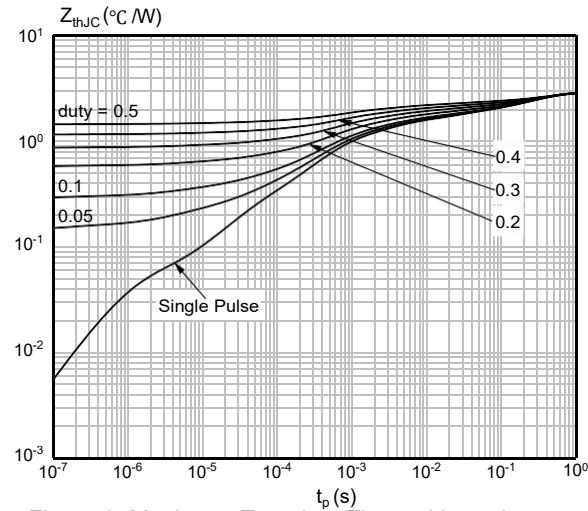


Figure 2. Maximum Transient Thermal Impedance

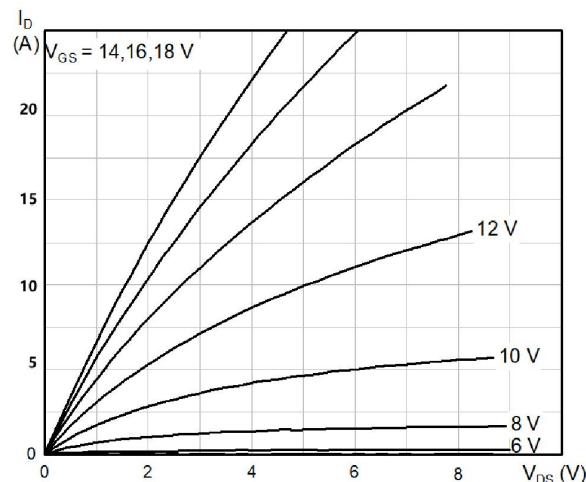


Figure 3. Typical Output Characteristics,  $T_J = 25^\circ\text{C}$

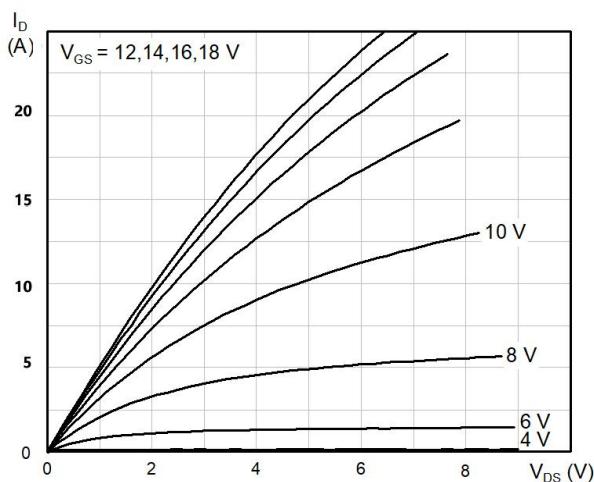


Figure 4. Typical Output Characteristics,  $T_J = 175^\circ\text{C}$

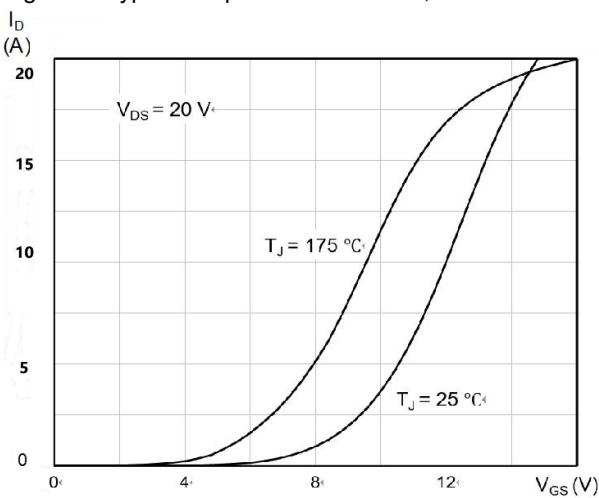


Figure 5. Typical Transfer Characteristics

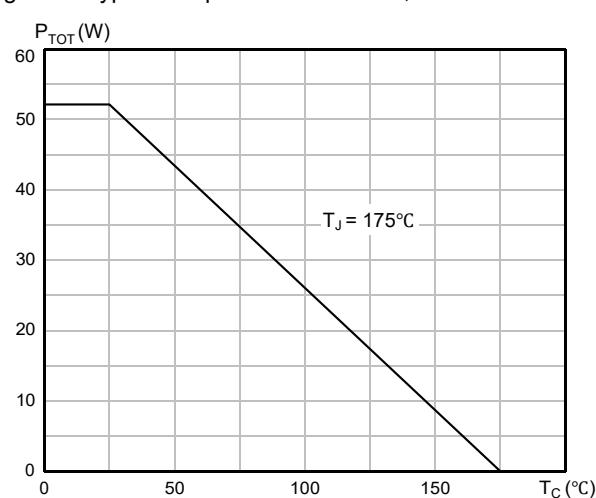
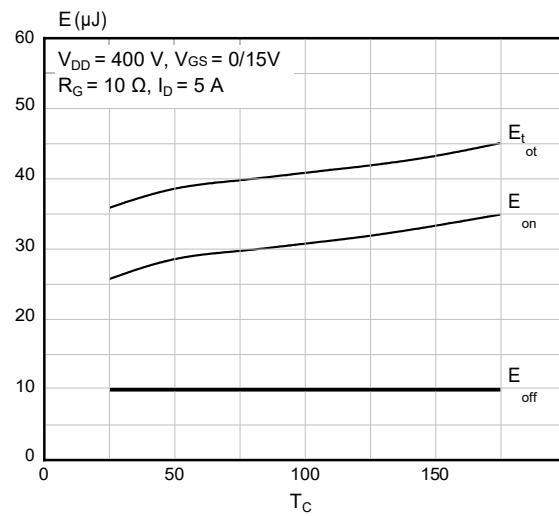
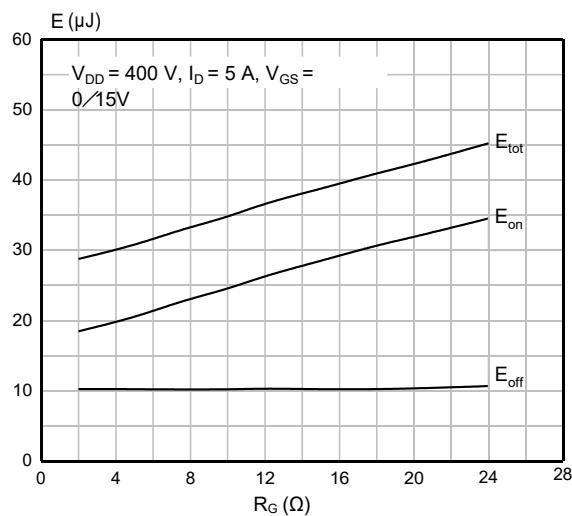
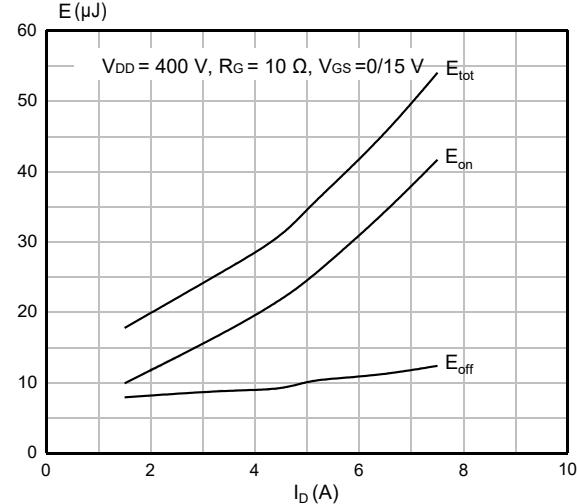
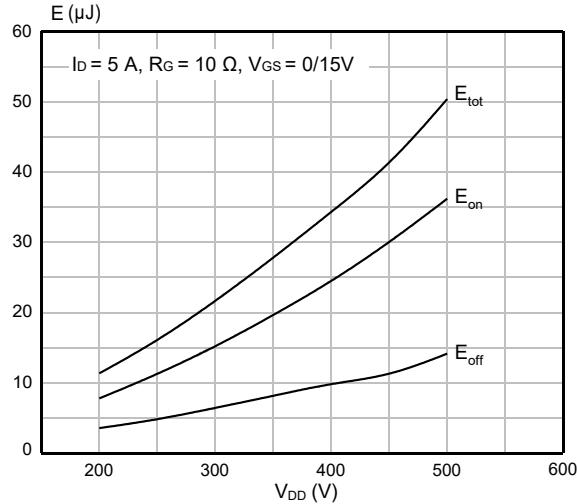
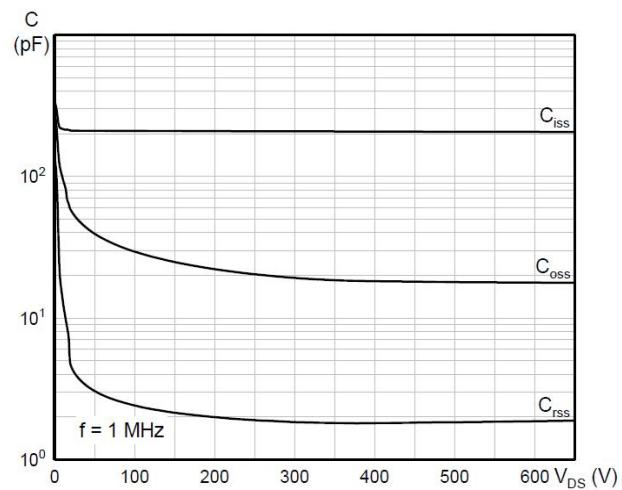
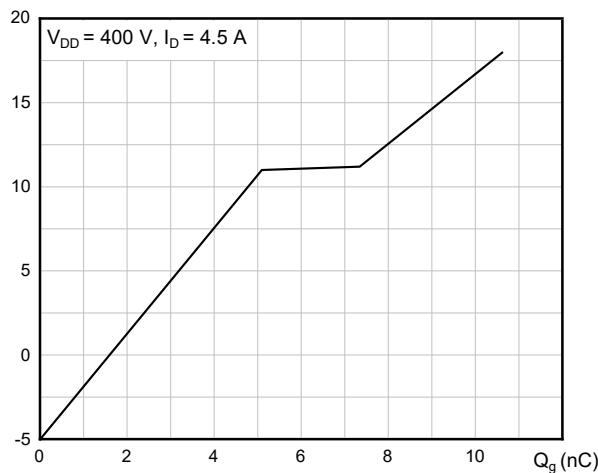
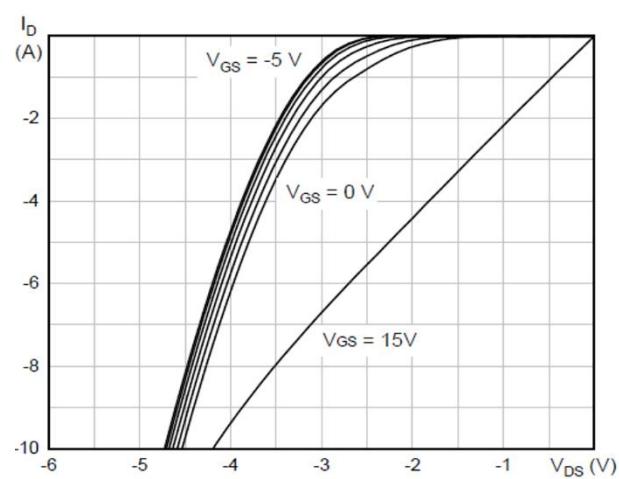
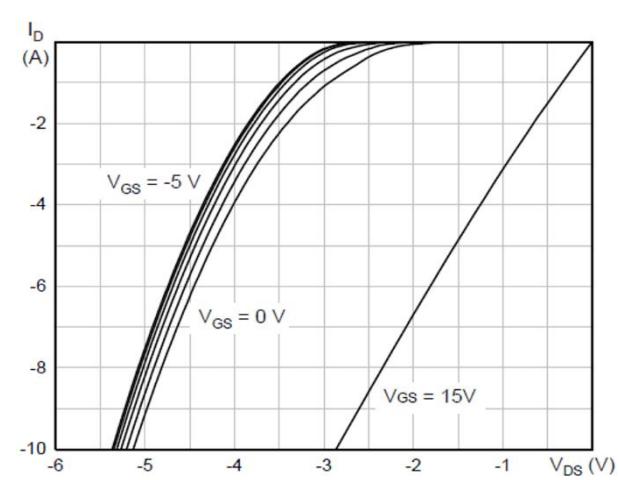
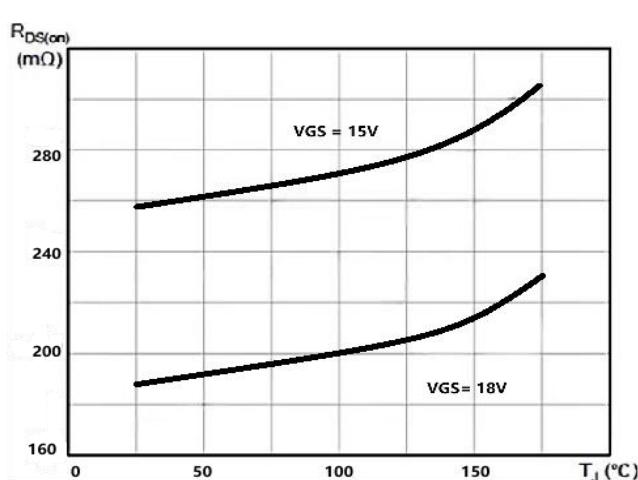
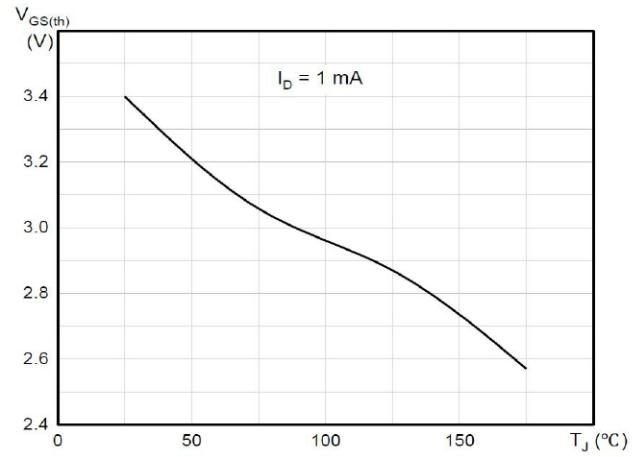
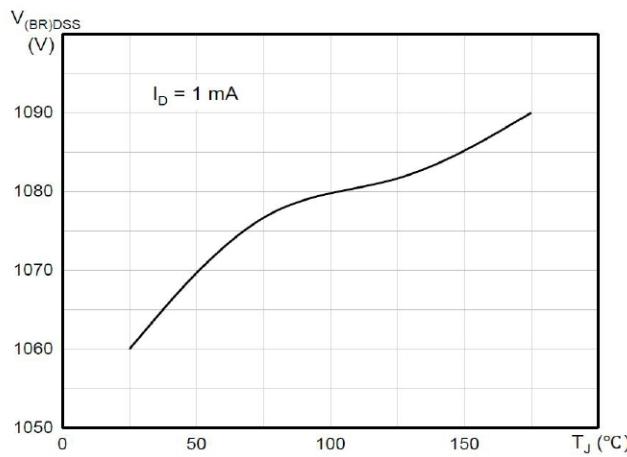


Figure 6. Total Power Dissipation

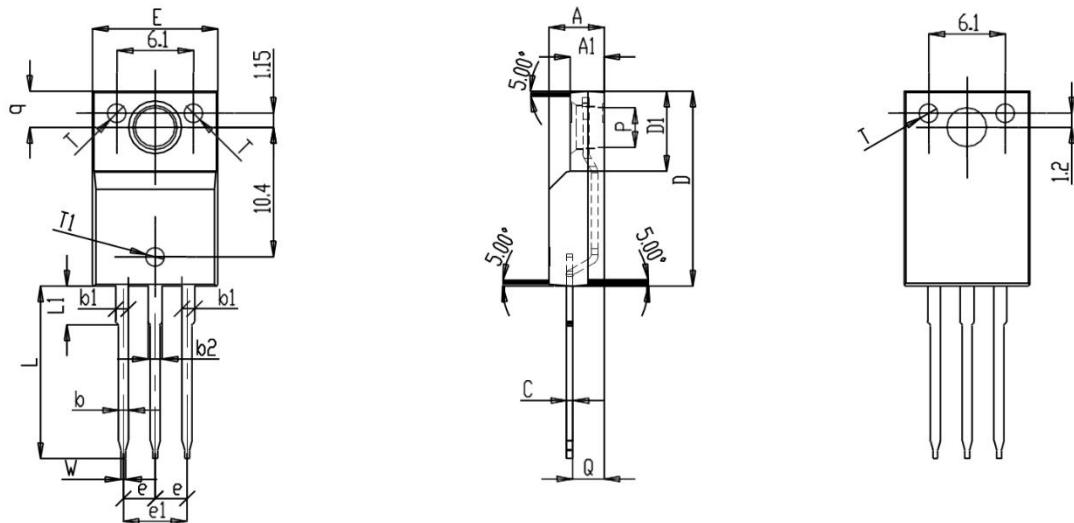






## Package Dimensions

Package TO-220F



SYMBOL	MILLIMETERS			NOTES	SYMBOL	MILLIMETERS			NOTES
	Normal	MIN.	MAX.			Normal	MIN.	MAX.	
A	4.4	4.2	4.6		e1	5.08	5	5.12	
A1	2.7	2.5	2.9		L	13.90	13.5	14.4	
b	0.8	0.7	0.9		L1	3.12	2.8	3.3	
b1	1.07	0.9	1.3		P	3.14	3.00	3.20	
b2	1.17	1	1.4		Q	2.44	2.3	2.6	
C	0.5	0.4	0.6		q	2.87	2.6	3	
D	15.63	15.4	15.8		W	0.37	0.3	0.5	
D1	6.22	6	6.4		T	1.52	1.3	1.7	
E	10.06	9.7	10.3		T1	1.20	1.1	1.3	
e	2.54	2.5	2.58						



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